



TPS51604-Q1 汽车应用中用于高频 CPU 内核功率的同步降压 场效应晶体管 (FET) 驱动器

1 特性

- 符合汽车应用要求
- 具有符合 AEC-Q100 的下列结果：
 - 器件温度等级 1: -40°C 至 125°C
 - 器件人体模型静电放电 (ESD) 分类等级 H2
 - 器件的充电器件模型 ESD 分类等级 C3B
- 针对已优化连续传导模式 (CCM) 的精简死区时间驱动电路
- 针对已优化断续传导模式 (DCM) 效率的自动零交叉检测
- 针对已优化轻负载效率的多个低功耗模式
- 为了实现高效运行的经优化信号路径延迟
- 针对超级本 (Ultrabook) FET 的集成 BST 开关驱动强度
- 针对 5V FET 驱动而进行了优化
- 转换输入电压范围 (V_{IN}): 4.5V 至 28V
- 2mm x 2mm 8 引脚晶圆级小外形无引线 (WSON) Power-Pad 封装

2 应用

- 汽车后座娱乐 (RSE) 平板电脑采用高频 CPU，配合以下电源输入使用：
 - 适配器
 - 电池
 - NVDC
 - 5V 至 12V 电源轨

3 说明

TPS51604-Q1 驱动器针对高频 CPU V_{CORE} 应用进行了优化。具有精简死区时间驱动和自动零交叉等高级特性，可用于在整个负载范围内优化效率。

$\overline{SKIP}$ 引脚提供立即 CCM 操作以支持输出电压的受控管理。此外，TPS51604-Q1 还支持两种低功耗模式。借助于三态 PWM 输入，静态电流可减少至 130 μ A，并支持立即响应。当 $\overline{SKIP}$ 保持在三态时，电流可减少至 8 μ A（恢复切换通常需要 20 μ s）。此驱动器与适当的德州仪器 (TI) 控制器配对使用，能够成为出色的高性能电源系统。

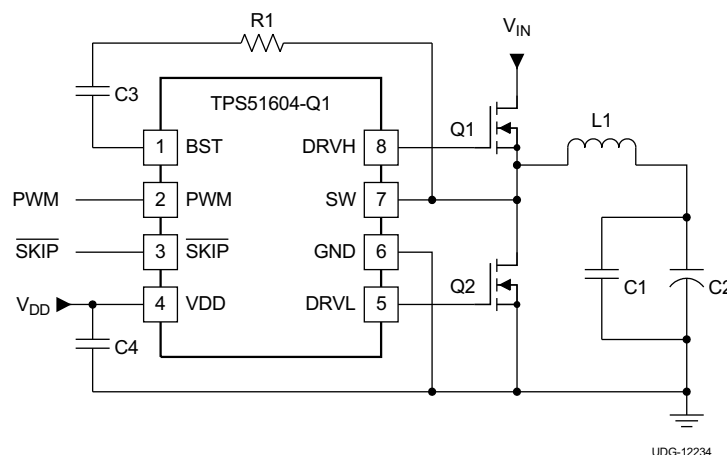
TPS51604-Q1 器件采用节省空间的耐热增强型 8 引脚 2mm x 2mm WSON 封装，工作温度范围为 -40°C 至 125°C。

器件信息⁽¹⁾

部件号	封装	封装尺寸（标称值）
TPS51604-Q1	WSON (8)	2.00mm x 2.00mm

(1) 要了解所有可用封装，请见数据表末尾的可订购产品附录。

简化电路原理图



UDG-12234



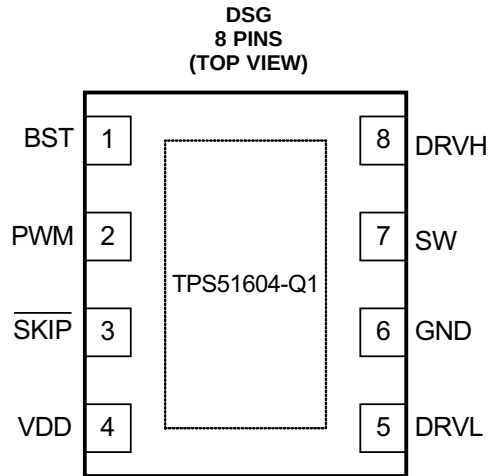
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4 修订历史记录

Changes from Original (January 2014) to Revision A	Page
• 已添加处理额定值表、特性描述部分、布局部分、器件和文档支持部分以及机械、封装和可订购信息部分	1
• Updated device name in <i>Thermal Information</i>	4
• Corrected temperature range for <i>Electrical Characteristics</i> specifications from 105°C to 125°C	5
• Corrected temperature range for <i>Electrical Characteristics</i> specifications from 105°C to 125°C	6

5 Pin Configuration and Functions



Pin Functions

PIN		I/O ⁽¹⁾	DESCRIPTION
NAME	NO.		
BST	1	I	High-side N-channel FET bootstrap voltage input; power supply for high-side driver
DRVH	8	O	High-side N-channel gate drive output
DRVL	5	O	Synchronous low-side N-channel gate drive output
GND	6	—	Synchronous low-side N-channel gate drive return and IC reference
PWM	2	I	PWM input. A tri-state voltage on this pin turns OFF both the high-side (DRVH) and low-side drivers (DRVL)
SKIP	3	I	When SKIP is LO, the zero crossing comparator is active; the power chain enters discontinuous conduction mode when the inductor current reaches zero. When SKIP is HI, the zero crossing comparator is disabled, and the driver outputs follow the PWM input. A tri-state voltage on SKIP puts the driver into a very-low power state.
SW	7	I/O	High-side N-channel gate drive return. Also, zero-crossing sense input
Thermal Pad		—	Tie to system GND plane with multiple vias
VDD	4	I	5-V power supply input; decouple to GND with a ceramic capacitor with a value of 1 μ F or greater

(1) I = Input, O = Output

6 Specifications

6.1 Absolute Maximum Ratings^{(1) (2)}

over operating free-air temperature (unless otherwise noted)

		MIN	MAX	UNIT
Input voltage	VDD	−0.3	6	V
	PWM, $\overline{\text{SKIP}}$	−0.3	6	
Output voltage	BST	−0.3	35	V
	BST (transient <20 ns)	−0.3	38	
	BST to SW; DRVH to SW	−0.3	6	
	SW	−2	30	
	DRVH, SW (transient <20 ns)	−5	38	
	DRVL	−0.3	6	
Ground pins	GND to PAD	−0.3	0.3	V
Operating junction temperature, T _J		−40	125	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values are with respect to the network ground terminal unless otherwise noted.

6.2 Handling Ratings

			MIN	MAX	UNIT
T _{stg}	Storage temperature range		−55	150	°C
V _(ESD)	Electrostatic discharge	Human body model (HBM), per AEC Q100-002 ⁽¹⁾	−2	2	kV
		Charged device model (CDM), per AEC Q100-011	−750	750	V

- (1) AEC Q100-002 indicates HBM stressing is done in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

6.3 Recommended Operating Conditions

Over operating free-air temperature range (unless otherwise noted)

		MIN	TYP	MAX	UNIT
Input voltage	VDD	4.5	5	5.5	V
	PWM, $\overline{\text{SKIP}}$	−0.1		5.5	
Output voltage	BST	−0.1		34	V
	BST to SW; DRVH to SW	−0.1		5.5	
	SW	−1		28	
	DRVL	−0.1		5.5	
Ground pins	GND to PAD	−0.1		0.1	V
Operating junction temperature, T _J		−40		125	°C

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		TPS51604-Q1 WSO8 (DSG) (8 PINS)	UNIT
R _{θJA}	Junction-to-ambient thermal resistance	63.1	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	74.1	
R _{θJB}	Junction-to-board thermal resistance	34.3	
ψ _{JT}	Junction-to-top characterization parameter	2.0	
ψ _{JB}	Junction-to-board characterization parameter	34.9	
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	11.7	

- (1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).

6.5 Electrical Characteristics

These specifications apply for $T_J = -40^{\circ}\text{C}$ to 125°C and $V_{DD} = 5\text{ V}$ unless otherwise specified.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
VDD INPUT SUPPLY						
I _{CC}	Supply current (operating)	$\overline{V_{SKIP}} = V_{VDD}$ or $\overline{V_{SKIP}} = 0\text{ V}$, PWM = High		160	600	μA
		$\overline{V_{SKIP}} = V_{VDD}$ or $\overline{V_{SKIP}} = 0\text{ V}$, PWM = Low		250		
		$\overline{V_{SKIP}} = V_{VDD}$ or $\overline{V_{SKIP}} = 0\text{ V}$, PWM = Float		130		
		$\overline{V_{SKIP}} = \text{Float}$		8		
VDD UNDERVOLTAGE LOCKOUT (UVLO)						
V _{UVLO}	UVLO threshold	Rising threshold		4.15		V
		Falling threshold	3.7			
V _{UVHYS}	UVLO hysteresis			0.2		V
PWM AND $\overline{\text{SKIP}}$ I/O SPECIFICATIONS						
R _I	Input impedance	Pullup to VDD		1.7		MΩ
		Pulldown (to GND)		800		kΩ
V _{IL}	Low-level input voltage			0.6		V
V _{IH}	High-level input voltage		2.65			
V _{IHH}	Hysteresis		0.2			
V _{TS}	Tri-state voltage		1.3		2.0	
t _{THOLD(off1)}	Tri-state activation time (falling) PWM		60		ns	
t _{THOLD(off2)}	Tri-state activation time (rising) PWM	60				
t _{TSKF}	Tri-state activation time (falling) $\overline{\text{SKIP}}$		1		μs	
t _{TSKR}	Tri-state activation time (rising) $\overline{\text{SKIP}}$		1			
t _{3RD(PWM)}	Tri-state exit time PWM		100		ns	
t _{3RD($\overline{\text{SKIP}}$)}	Tri-state exit time $\overline{\text{SKIP}}$		50		μs	
HIGH-SIDE GATE DRIVER (DRVH)						
t _{R(DRVH)}	Rise time	DRVH rising, C _{DRVH} = 3.3 nF; 20% to 80%		30		ns
t _{RPD(DRVH)}	Rise time propogation delay	C _{DRVH} = 3.3 nF		40		ns
R _{SRC}	Source resistance	Source resistance, (V _{BST} – V _{SW}) = 5 V, high state, (V _{BST} – V _{DRVH}) = 0.1 V		4	8	Ω
t _{F(DRVH)}	Fall time	DRVH falling, C _{DRVH} = 3.3 nF		8		ns
t _{FPD(DRVH)}	Fall-time propagation delay	C _{DRVH} = 3.3 nF		25		ns
R _{SNK}	Sink resistance	Sink resistance, (V _{BST} – V _{SW}) forced to 5 V, low state (V _{DRVH} – V _{SW}) = 0.1 V		0.5	1.6	Ω
R _{DRVH}	DRVH to SW resistance ⁽¹⁾			100		kΩ
LOW-SIDE GATE DRIVER (DRV _L)						
t _{R(DRV_L)}	Rise time	DRV _L rising, C _{DRV_L} = 3.3 nF; 20% to 80%		15		ns
t _{RPD(DRV_L)}	Rise time propagation delay	C _{DRV_L} = 3.3 nF		35		ns
R _{SRC}	Source resistance	Source resistance, (V _{VDD} –GND) = 5 V, high state, (V _{VDD} – V _{DRV_L}) = 0.1 V		1.5	3	Ω
t _{F(DRV_L)}	Fall time	DRV _L falling, C _{DRV_L} = 3.3 nF		10		ns
t _{FPD(DRV_L)}	Fall-time propagation delay	C _{DRV_L} = 3.3 nF		15		ns
R _{SNK}	Sink resistance	Sink resistance, (V _{VDD} – GND) = 5 V, low state, (V _{DRV_L} – GND) = 0.1 V		0.4	1.6	Ω
R _{DRV_L}	DRV _L to GND resistance ⁽¹⁾			100		kΩ

(1) Specified by design. Not production tested.

TPS51604-Q1

ZHCSCU0A – JANUARY 2014 – REVISED AUGUST 2014

www.ti.com.cn
Electrical Characteristics (接下页)

 These specifications apply for $T_J = -40^{\circ}\text{C}$ to 125°C and $V_{DD} = 5\text{ V}$ unless otherwise specified.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
GATE DRIVER DEAD-TIME						
$t_{R(DT)}$	Rising edge		0	20	35	ns
$t_{F(DT)}$	Falling edge		0	10	25	ns
ZERO CROSSING COMPARATOR						
V_{ZX}	Zero crossing offset	SW voltage rising	-2.25	0	2.00	mV
BOOTSTRAP SWITCH						
V_{FBST}	Forward voltage	$I_F = 10\text{ mA}$		120	240	mV
I_{RLEAK}	Reverse leakage	$(V_{BST} - V_{DD}) = 25\text{ V}$			2	μA
$R_{DS(on)}$	On-resistance			12	24	Ω

6.6 Typical Characteristics

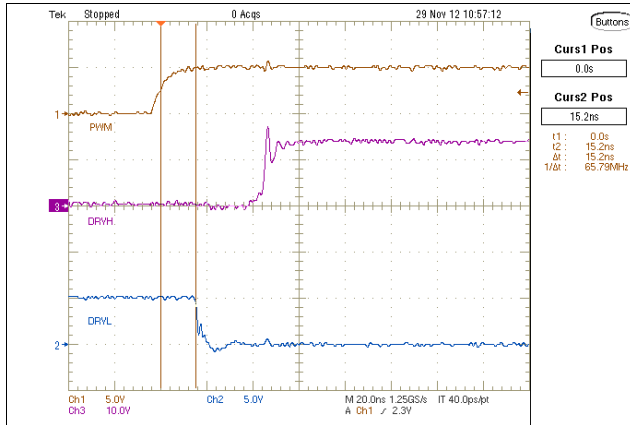


图 1. PWM High to DRVH Low

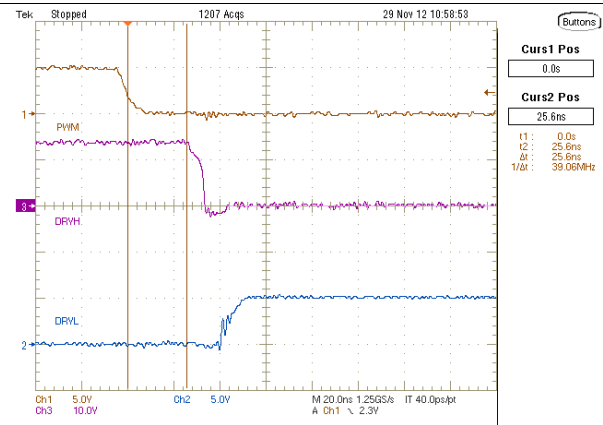


图 2. PWM Low to DRVH Low

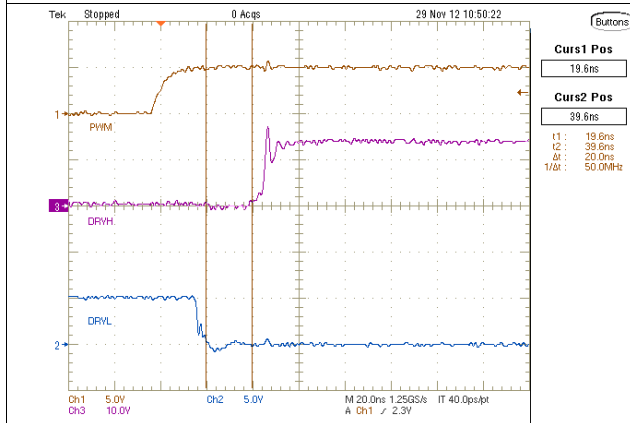


图 3. DRVH Low to DRVH High

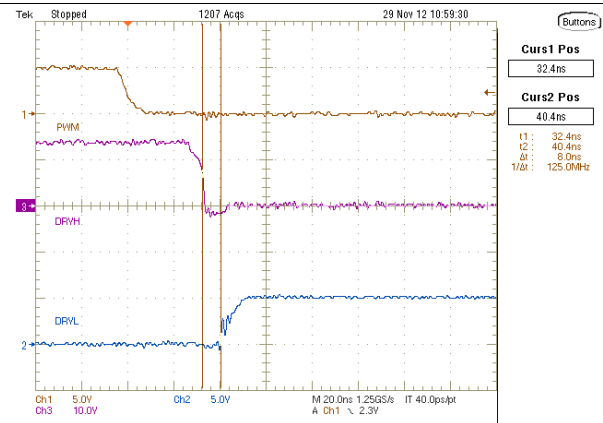


图 4. DRVH Low to DRVH High

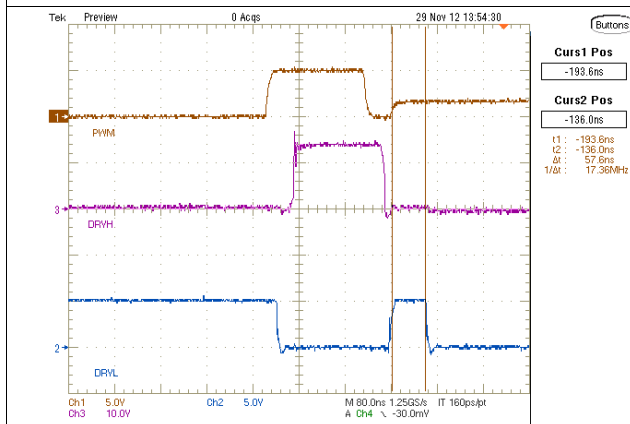


图 5. PWM Low to Tri-State

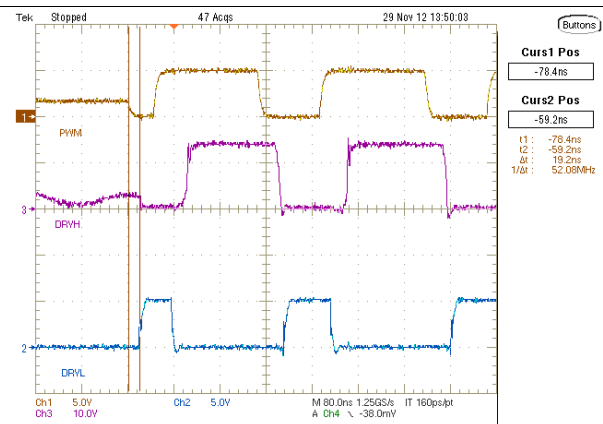
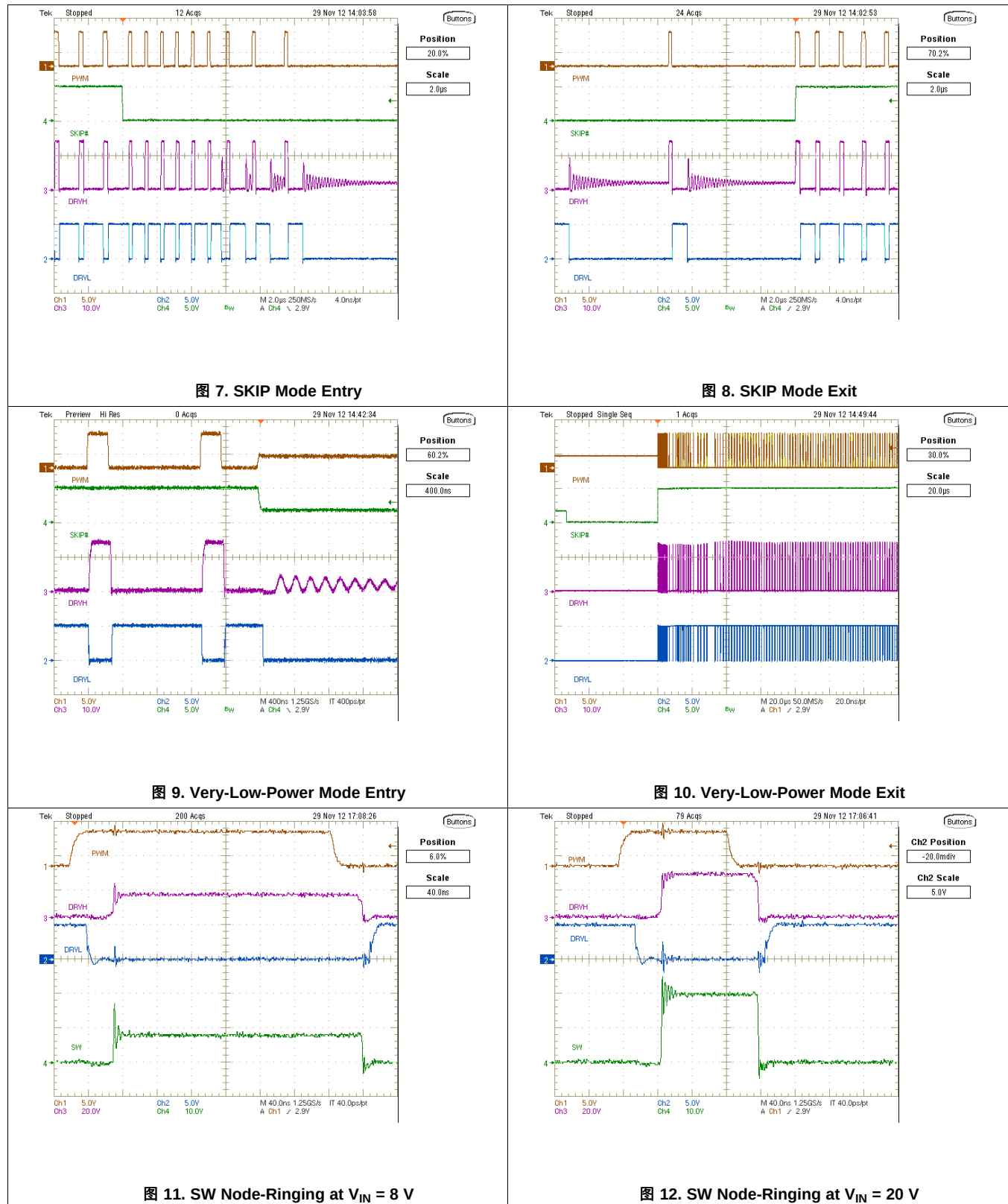


图 6. PWM Tri-State to Low

Typical Characteristics (接下页)



6.7 Typical Power Block MOSFET Characteristics

Power block MOSFET: CSD87330 (SLPS284), Inductor: 0.22 μ F, 1.1-m Ω DCR

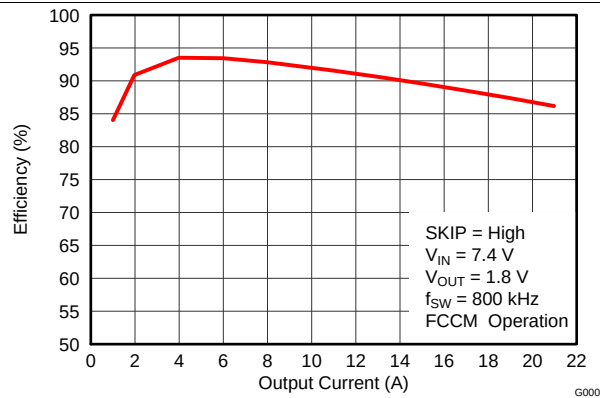


图 13. Efficiency vs Output Current, SKIP = High

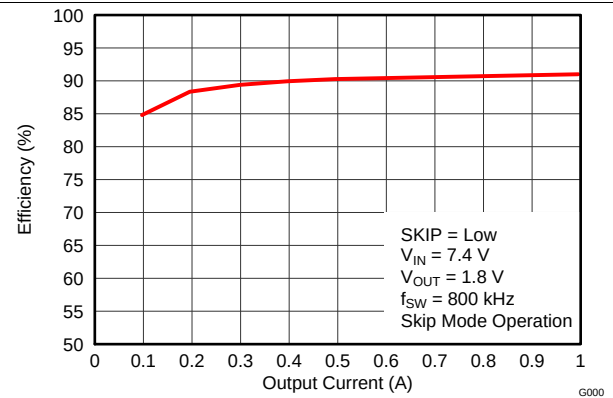


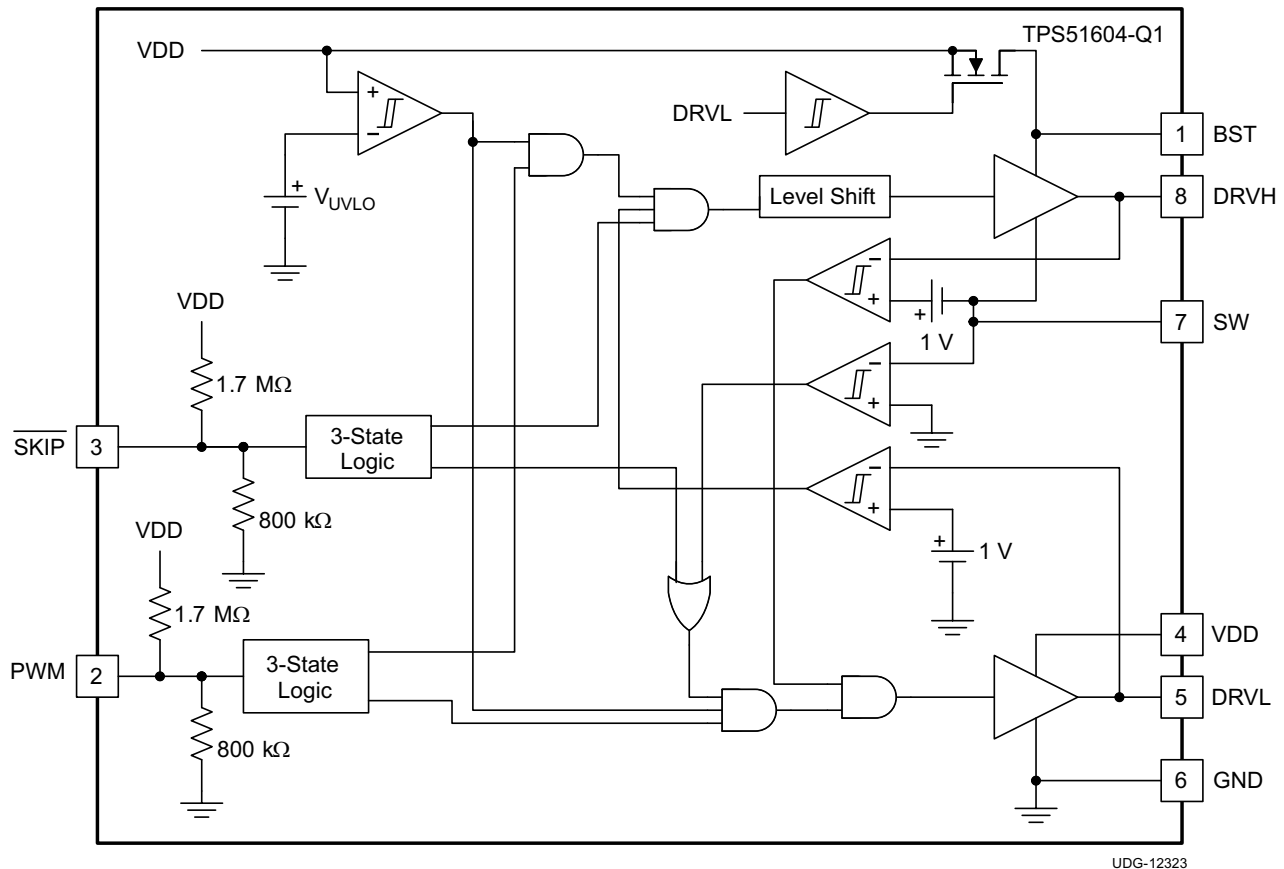
图 14. Efficiency vs Output Current, SKIP = Low

7 Detailed Description

7.1 Overview

The TPS51604-Q1 device is a synchronous-buck MOSFET driver designed to drive both high-side and low-side MOSFETs. It allows high-frequency operation with current driving capability matched to the application. The integrated boost switch is internal. The TPS51604-Q1 device employs dead-time reduction control and shoot-through protection, which helps avoid simultaneous conduction of high-side and low-side MOSFETs. Also, the drivers improve light-load efficiency with integrated DCM-mode operation using adaptive crossing detection. Typical applications yield a steady-state duty cycle of 60% or less. For high steady-state duty cycle applications, including a small external Schottky diode may help to ensure sufficient charging of the bootstrap capacitor.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 UVLO Protection

The UVLO comparator evaluates the VDD voltage level. As V_{DD} rises, both DRVH and DRVL hold actively low at all times until V_{DD} reaches the higher UVLO threshold (V_{UVLO_H}). Then, the driver becomes operational and responds to PWM and SKIP commands. If VDD falls below the lower UVLO threshold ($V_{UVLO_L} = V_{UVLO_H} - \text{Hysteresis}$), the device disables the driver and drives the outputs of DRVH and DRVL actively low. 图 15 shows this function.

CAUTION

Do not start the driver in the very low power mode ($\overline{\text{SKIP}} = \text{Tri-state}$).

Feature Description (接下页)

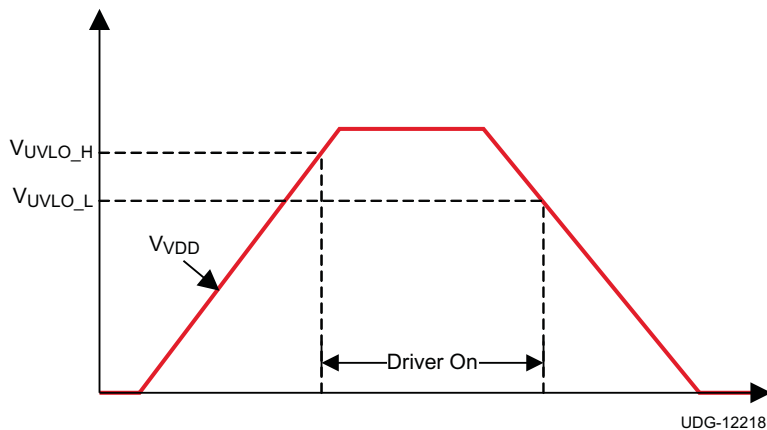


图 15. UVLO Operation

7.3.2 PWM Pin

The PWM pin incorporates an input tri-state function. The device forces the gate driver outputs to low when PWM is driven into the tri-state window and the driver enters a low power state with zero exit latency. The pin incorporates a weak pullup to maintain the voltage within the tri-state window during low-power modes. Operation into and out of tri-state mode follows the timing diagram outlined in 图 16.

When VDD reaches the UVLO_H level, a tri-state voltage range (window) is set for the PWM input voltage. The window is defined as the PWM voltage range between PWM logic high (V_{IH}) and logic low (V_{IL}) thresholds. The device sets high-level input voltage and low-level input voltage threshold levels to accommodate both 3.3-V (typical) and 5-V (typical) PWM drive signals.

When the PWM exits tri-state, the driver enters CCM for a period of 4 μ s, regardless of the state of the $\overline{SKIP}$ pin. Typical operation requires this time period in order for the auto-zero comparator to resume.

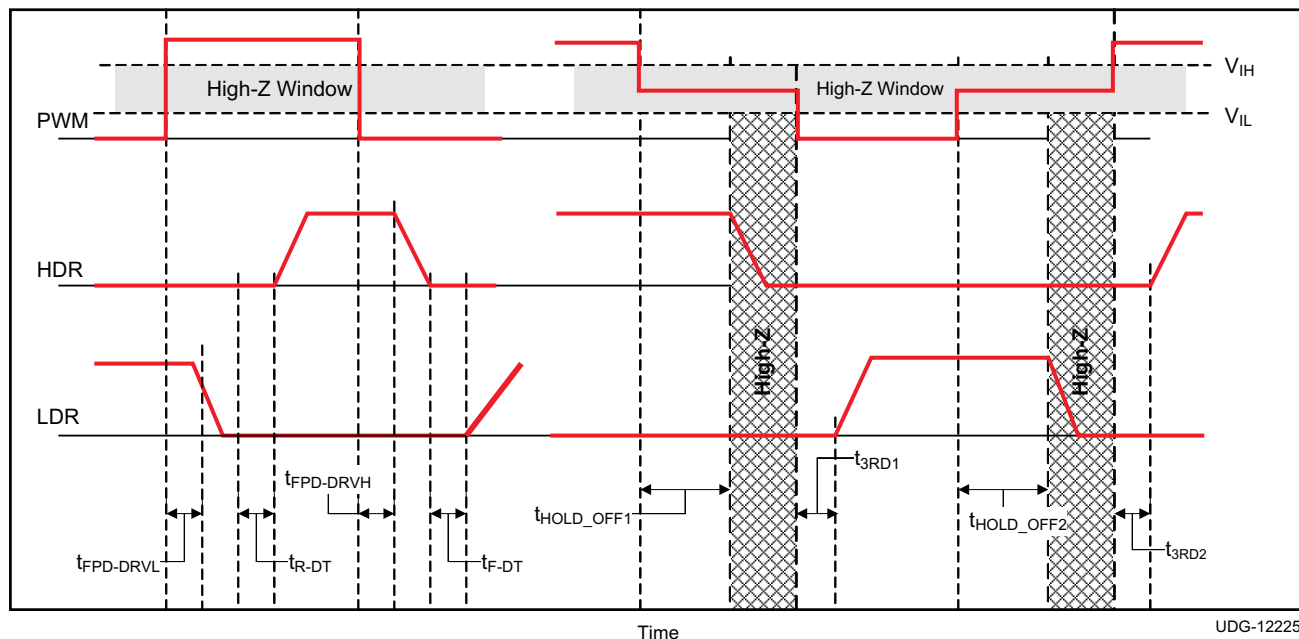


图 16. PWM Tri-State Timing Diagram

Feature Description (接下页)

7.3.3 $\overline{\text{SKIP}}$ Pin

The $\overline{\text{SKIP}}$ pin incorporates the input tri-state buffer as PWM. The function is somewhat different. When $\overline{\text{SKIP}}$ is low, the zero crossing (ZX) detection comparator is enabled, and DCM mode operation occurs if the load current is less than the critical current. When $\overline{\text{SKIP}}$ is high, the ZX comparator disables, and the converter enters FCCM mode. When both $\overline{\text{SKIP}}$ and PWM are tri-stated, typical operation forces the gate driver outputs low and the driver enters a very-low-power state. In the low-power state, the UVLO comparator remains off to reduce quiescent current. When either $\overline{\text{SKIP}}$ is pulled low, the driver wakes up and is able to accept PWM pulses in less than 50 μs .

表 1 shows the logic functions of UVLO, PWM, $\overline{\text{SKIP}}$, DRVH, and DRVL.

表 1. Logic Functions of the TPS51604-Q1

UVLO	PWM	$\overline{\text{SKIP}}$	DRVL	DRVH	MODE
Active	—	—	Low	Low	Disabled
Inactive	Low	Low	High ⁽¹⁾	Low	DCM ⁽¹⁾
Inactive	Low	High	High	Low	FCCM
Inactive	High	H or L	Low	High	
Inactive	Tri-state	H or L	Low	Low	Low power
Inactive	—	Tri-state	Low	Low	Very-low power

(1) Until zero crossing protection occurs.

7.3.3.1 Zero Crossing (ZX) Operation

The zero crossing comparator is adaptive for improved accuracy. As the output current decreases from a heavy load condition, the inductor current also reduces and eventually arrives at a *valley*, where it touches zero current, which is the boundary between continuous conduction and discontinuous conduction modes. The SW pin detects the zero-current condition. When this zero inductor current condition occurs, the ZX comparator turns off the rectifying MOSFET.

7.3.4 Adaptive Dead-Time Control and Shoot-Through Protection

The driver utilizes an anti-shoot-through and adaptive dead-time control to minimize low-side body diode conduction time and maintain high efficiency. When the PWM input voltage becomes high, the low-side MOSFET gate voltage begins to fall after a propagation delay. At the same time, DRVL voltage is sensed, and high-side driving voltage starts to increase after DRVL voltage is lower than a proper threshold.

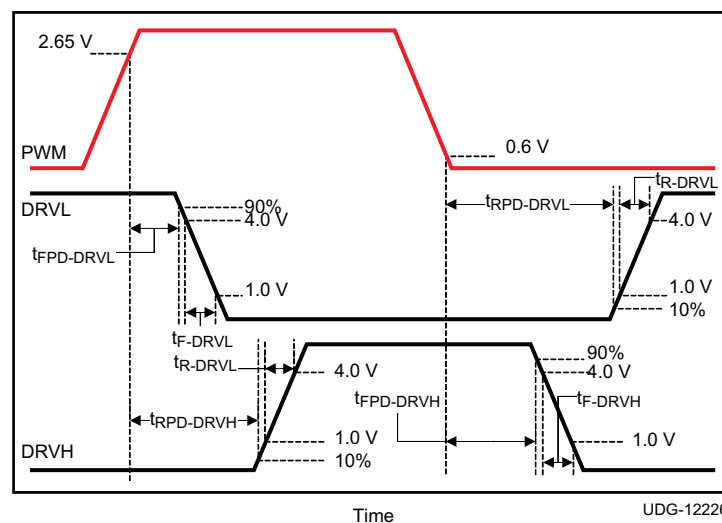


图 17. Rise and Fall Timing and Propagation Delay Definitions

Typical operation manages to near zero the dead-time between the low-side gate turn-off to high-side gate voltage turn-on, and high-side gate turn-off to low-side gate turn-on, in order to avoid simultaneous conduction of both MOSFETs, as well as to reduce body diode conduction and recovery losses. This operation also reduces ringing on the leading edge of the SW waveform.

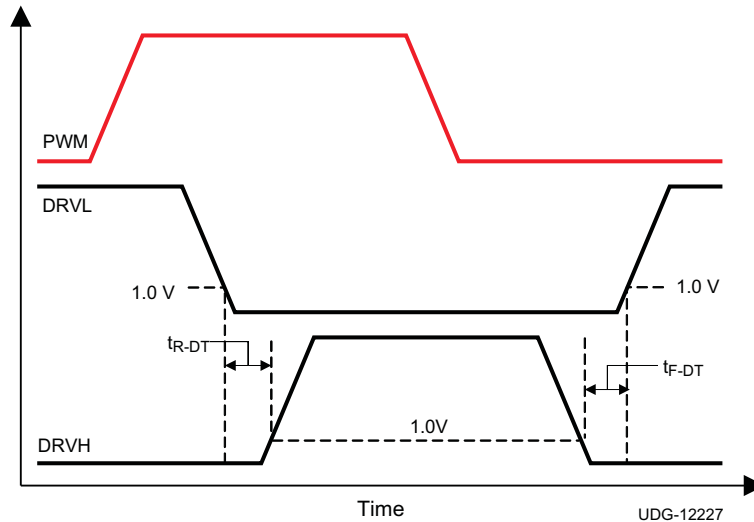


图 18. Dead-Time Definitions

7.3.5 Integrated Boost-Switch

To maintain a BST-SW voltage close to VDD (to get lower conduction losses on the high-side FET), the conventional diode between the VDD pin and BST pin is replaced by a FET, which is gated by the DRVL signal.

8 Layout

8.1 Layout Guidelines

To improve the switching characteristics and design efficiency, these layout rules must be considered:

- Locate the driver as close as possible to the MOSFETs.
- Locate the VDD and bootstrap capacitors as close as possible to the driver.
- Pay special attention to the GND trace. Use the thermal pad of the package as the GND by connecting it to the GND pin. The GND trace or pad from the driver goes directly to the source of the MOSFET, but should not include the high current path of the main current flowing through the drain and source of the MOSFET.
- Use a similar rule for the switch-node as for the GND.
- Use wide traces for DRVH and DRVL closely following the related SW and GND traces. A width of between 80 and 100 mils is preferable where possible.
- Place the bypass capacitors as close as possible to the driver.
- Avoid PWM and enable traces going close to the SW and pad where high dV/dT voltage can induce significant noise into the relatively high-impedance leads.

A poor layout can decrease the reliability of the entire system.

9 器件和文档支持

9.1 商标

All trademarks are the property of their respective owners.

9.2 静电放电警告



这些装置包含有限的内置 ESD 保护。存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

9.3 术语表

[SLYZ022](#) — TI 术语表。

这份术语表列出并解释术语、首字母缩略词和定义。

10 机械封装和可订购信息

以下页中包括机械封装和可订购信息。 这些信息是针对指定器件可提供的最新数据。 这些数据会在无通知且不对本文档进行修订的情况下发生改变。 欲获得该数据表的浏览器版本，请查阅左侧的导航栏。

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TPS51604QDSGRQ1	Active	Production	WSO (DSG) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	604Q
TPS51604QDSGRQ1.A	Active	Production	WSO (DSG) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	604Q
TPS51604QDSGTQ1	Active	Production	WSO (DSG) 8	250 SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	604Q
TPS51604QDSGTQ1.A	Active	Production	WSO (DSG) 8	250 SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	604Q

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "-" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

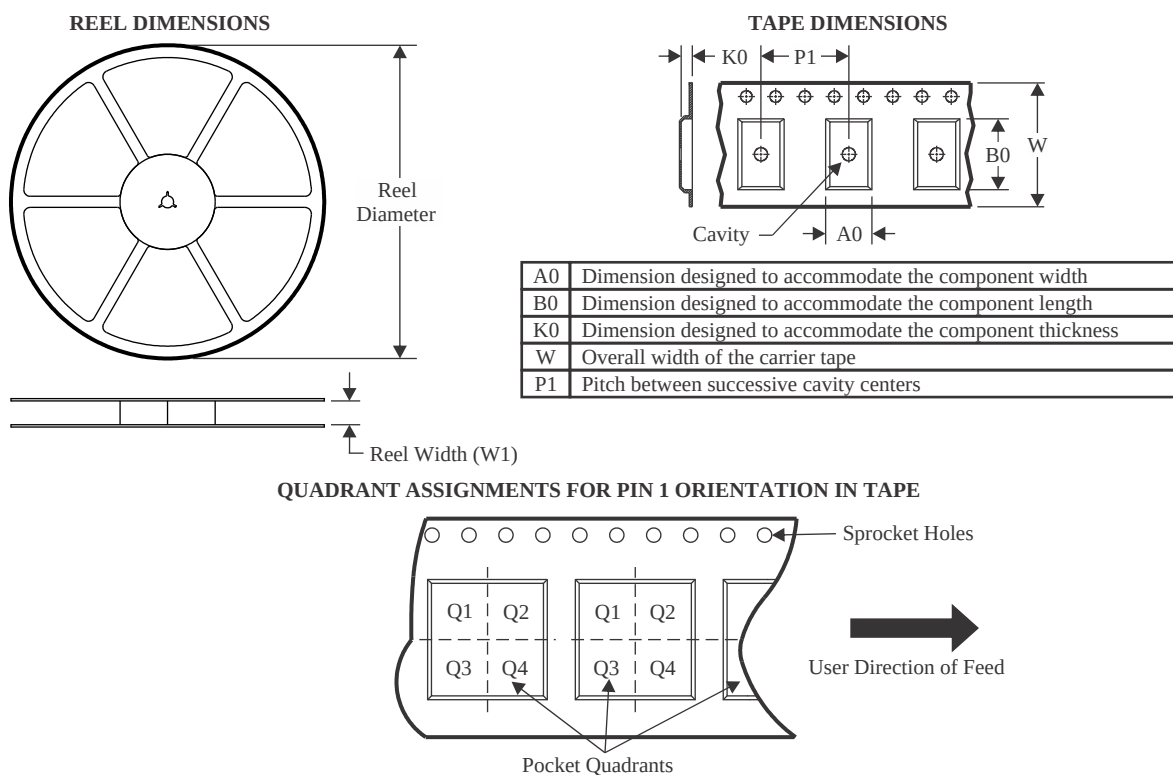
OTHER QUALIFIED VERSIONS OF TPS51604-Q1 :

- Catalog : [TPS51604](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product

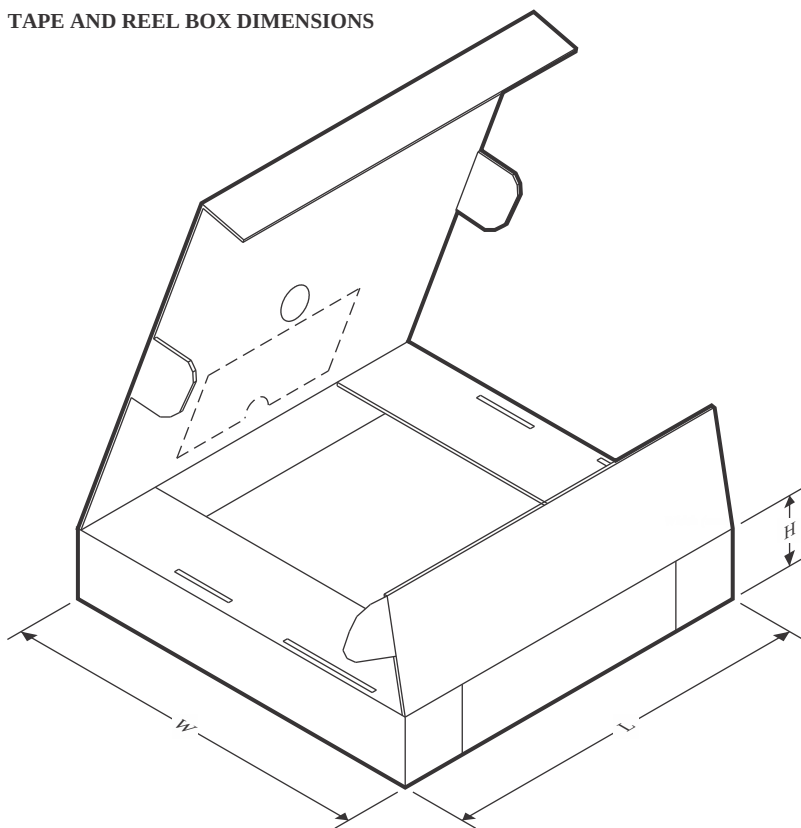
TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS51604QDSGRQ1	WSO	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TPS51604QDSGRQ1	WSO	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TPS51604QDSGTQ1	WSO	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TPS51604QDSGTQ1	WSO	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS51604QDSGRQ1	WSN	DSG	8	3000	210.0	185.0	35.0
TPS51604QDSGRQ1	WSN	DSG	8	3000	210.0	185.0	35.0
TPS51604QDSGTQ1	WSN	DSG	8	250	210.0	185.0	35.0
TPS51604QDSGTQ1	WSN	DSG	8	250	210.0	185.0	35.0

GENERIC PACKAGE VIEW

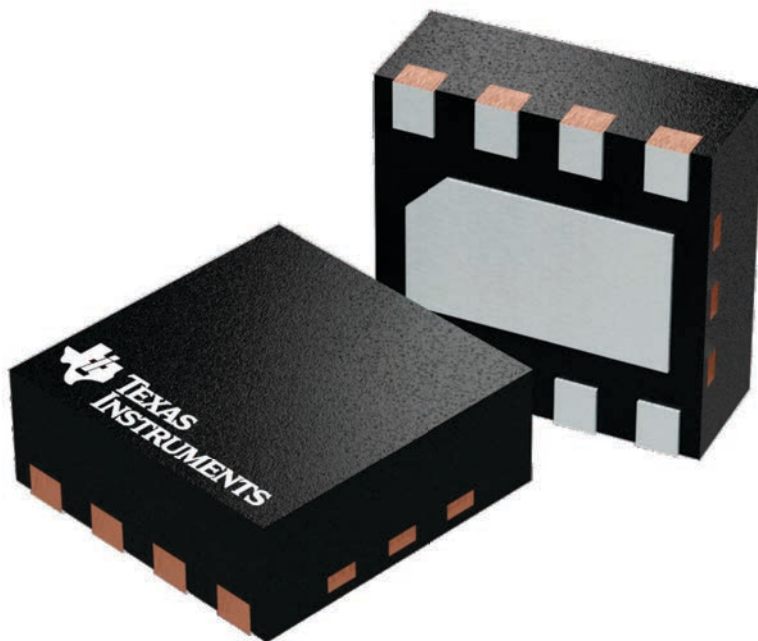
DSG 8

WSON - 0.8 mm max height

2 x 2, 0.5 mm pitch

PLASTIC SMALL OUTLINE - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

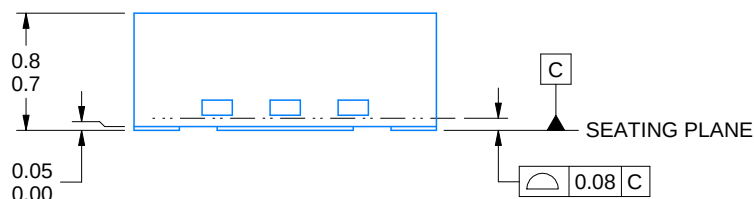


4224783/A



WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD

[illegible]

→| |← (DIM A) TYP

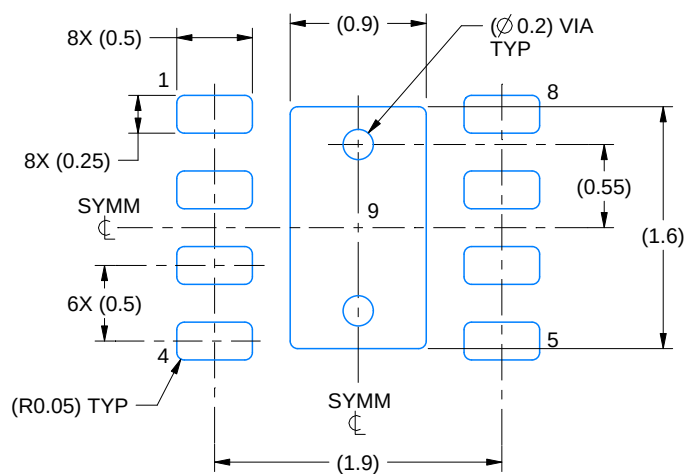
4218900/E 08/2022

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

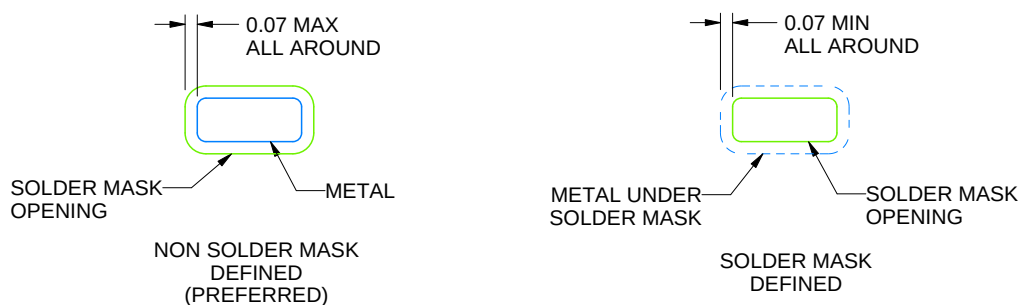
DSG0008A

WSN - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



LAND PATTERN EXAMPLE
SCALE:20X



SOLDER MASK DETAILS

4218900/E 08/2022

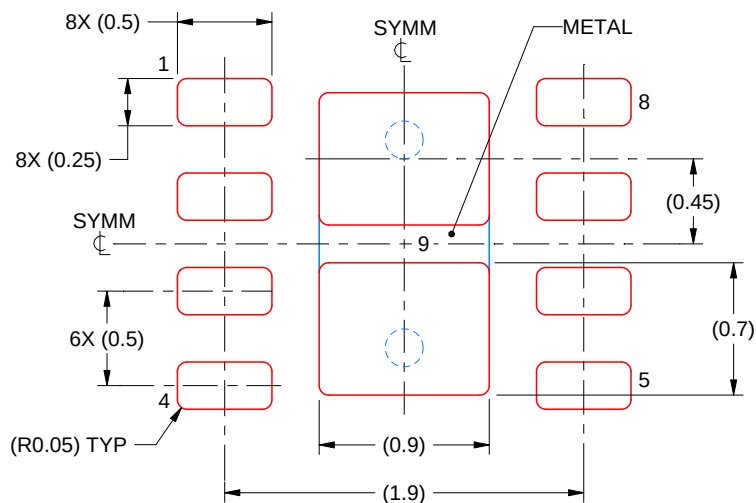
NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

DSG0008A

WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



SOLDER PASTE EXAMPLE BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD 9:
87% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE
SCALE:25X

4218900/E 08/2022

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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